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PTO/SB/08A (08-03)

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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Sheet **1** of **5****Complete if Known**

Application Number	10/678,438
Filing Date	3 October 2003
First Named Inventor	Vladimir V. MAKAROV
Art Unit	
Examiner Name	
Attorney Docket Number	65.0395

**U. S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
		US- 5,840,630	11-24-1998	Cecere et al.	
		US- 6,514,866 B2	02-04-2003	Russell et al.	
		US- 2003/0060048 A1	03-27-2003	Russell et al.	
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		US- 6,407,001 B1	06-18-2002	Scott	
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		US- 5,959,358	09-28-1999	Lanford et al.	

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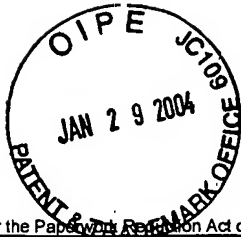
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages Or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
		JP2295117	12-06-1990	NTT ✓		✓
		JP4173988	11-02-1990	Nissin Electric ✓		✓

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Art Unit	
Examiner Name	
Attorney Docket Number	65.0395

Sheet 3 of 5

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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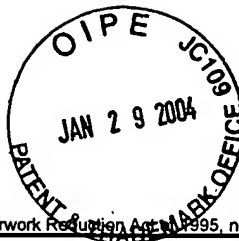
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		J. Gonzalez et al, Improvements in Focused Ion Beam Micro-machining of Interconnect Materials, J. Vac. Sci. Technol. B20(6), Nov/Dec 2002, pp. 2700-2704	
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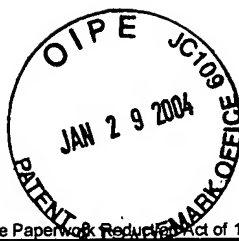
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